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PATENT APPLICATION  
Attorney's Doc. No. 9898-287

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent No.: 6,794,711  
Inventor: Kang et al.  
Issued: September 21, 2004

For: NON-VOLATILE MEMORY DEVICE HAVING SELECT TRANSISTOR  
STRUCTURE AND SONOS CELL STRUCTURE AND METHOD FOR  
FABRICATING THE DEVICE

Ser. No.: 10/620,025  
Group Art Unit: 2818

Filed: July 14, 2003  
Examiner: Andy Huynh

TRANSMITTAL LETTER

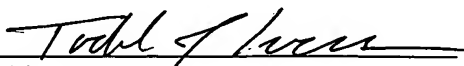
Commissioner for Patents  
P.O. Box 1450  
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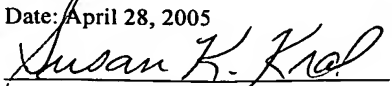
- ☒ Request for Certificate of Correction
- ☒ Certificate of Correction Form PTO 1050
- ☒ Return postcard
- ☒ Any deficiency or overpayment should be charged or credited to deposit account number 13-1703.

Respectfully submitted,

MARGER JOHNSON & McCOLLOM, P.C.

  
Todd J. Iverson  
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Susan K. Kral



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REQUEST FOR CERTIFICATE OF CORRECTION


Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Upon comparison of the above-identified original Letters Patent with applicant's copy of the application therefor, the following errors in the original Letters Patent have been noted:

Column 4, line 36, "the select transistor" should read --the select transistor II.--.  
Column 5, line 56, "transistor II. The" should read --transistor III. The--.  
Column 6, line 43, "transistor m. At" should read --transistor III. At--.  
Column 7, line 12, "transistor m is" should read --transistor III is--.  
Column 7, line 23, "transistor m. Therefore," should read --transistor III. Therefore,--.  
Column 7, line 33, "transistor m. Their" should read --transistor III. Their--.  
Column 7, line 60, "transistor m is" should read --transistor III is--.  
Column 18, line 43, "among sidewall, of" should read --among sidewalls of--.  
Column 18, line 46, "gate structure an the" should read --gate structure on the--.

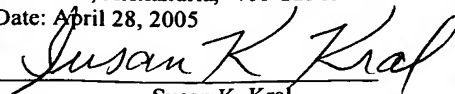
Applicant respectfully requests that a Certificate of Correction calling attention to the above errors be issued pursuant to Rule 322 of the Patent Office and Title 35, United States Code, Section 254. Two copies of a Certificate of Correction form are enclosed.

Respectfully submitted,  
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Susan K. Kral

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(Also Form PTO-1050)

## UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 6,794,711  
DATED : September 21, 2004  
INVENTOR(S) : Kang et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

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Column 18, line 43, "among sidewall, of" should read --among sidewalls of--.

Column 18, line 46, "gate structure an the" should read --gate structure on the--.

MAILING ADDRESS OF SENDER:

Marger Johnson & McCollom  
1030 S.W. Morrison Street  
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PATENT NO. 6,794,711

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